

Features:

- RoHS Complaint
- 100 Watts
- DC 4.0 GHz
- AIN Ceramic
- Non-Nichrome
 Resistive
- Low VSWR
- 100% Tested

Description:

The K100N50X4B is high performance Aluminum Nitride (AIN) half flange termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power combiners. The termination is also RoHS compliant!

General Specifications:

Resistive Element	Thick Film
Substrate	AIN Ceramic
Mounting Flange	Copper, nickel plated per QC-N-290
Operating Temperature	-55°C to +150°C (see de rating chart)

Electrical Specifications:

 Resistance Value:
 50 Ohms, ± 2%

 Power:
 100 Watts

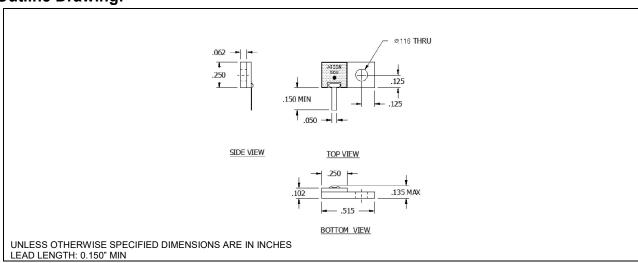
 Frequency Range:
 DC − 4.0 GHz

 Return Loss
 > 26 dB to 1.3 GHz

 > 22 dB to 4.0 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change without notice.**

Outline Drawing:

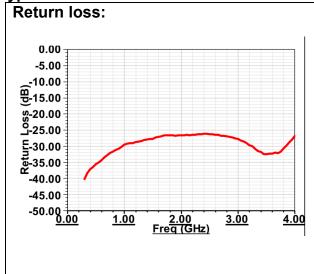


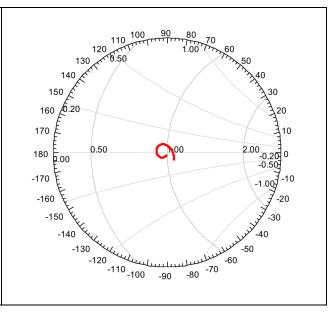
Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.



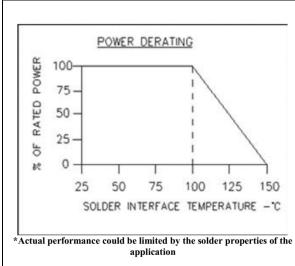


Typical Performance:

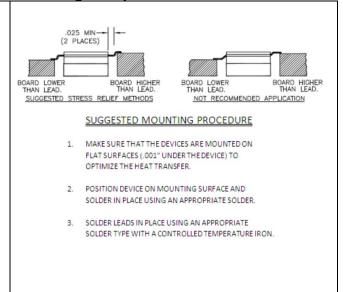




Power de-rating:



Mounting Footprint:



Contact us:

rf&s_support@ttm.com